

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1425	(118/52).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L2	153	(118/676).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L3	262	(118/669).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L4	220	(118/713).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L5	764	(118/56).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L6	266	(396/611).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L7	1	("6261007").PN.	USPAT	OR	OFF	2005/01/20 16:44
L8	9	"6261007"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44
L9	466	(396/604).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L10	1	("63302521").PN.	JPO	OR	OFF	2005/01/20 16:44

L11	952	(118/301).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L12	2276	(134/902).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L13	2493	(118/50).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:44
L14	0	("9164364").PN.	JPO	OR	OFF	2005/01/20 16:44
L15	99	"118"/\$.ccls. and tokyo.asn. and humidity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44
L16	203	"118"/\$.ccls. and tokyo.asn. and (reduced near2 pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44
L17	15	"118"/\$.ccls. and tokyo.asn. and (reduced near2 pressure) and humidity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44
L18	1	"09164364"	JPO	OR	ON	2005/01/20 16:44
L19	1	("63010528").PN.	JPO	OR	OFF	2005/01/20 16:44
L20	1	"09002113"	JPO	OR	ON	2005/01/20 16:44
L21	1	("6112430").PN.	USPAT	OR	OFF	2005/01/20 16:44
L22	1	("5670210").PN.	USPAT	OR	OFF	2005/01/20 16:44
L23	1	("5641541").PN.	USPAT	OR	OFF	2005/01/20 16:44
L24	1	"09002114"	JPO	OR	ON	2005/01/20 16:44
L25	9	"5779779"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44

L26	1	("10173229").PN.	JPO	OR	OFF	2005/01/20 16:44
L27	8	((("6063190") or ("6033480") or ("5804046") or ("5662785") or ("5578127") or ("5059266") or ("4633804") or ("6159541"))).PN.	USPAT	OR	OFF	2005/01/20 16:44
L28	9	"6159541"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44
L29	1	("11259895").PN.	JPO	OR	OFF	2005/01/20 16:44
L30	1	("11260431").PN.	JPO	OR	OFF	2005/01/20 16:44
L31	1	("10163229").PN.	JPO	OR	OFF	2005/01/20 16:44
L32	82	tokyo.asn. and ((reduced near2 pressure) near10 drying)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44
L33	61	(photoresist near3 coat\$3) and ((reduced near2 pressure) near10 drying)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44
L34	13	(photoresist near3 coat\$3) and ((low near2 pressure) near10 drying)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44
L35	12	tokyo.asn. and ((low near2 pressure) near10 drying)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:44
L36	39	"118"/\$.ccls. and tokyo.asn. and ((reduced near2 pressure) near10 unit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L37	316	tokyo.asn. and adhesion and "118"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L38	1	("6599366").PN.	USPAT	OR	OFF	2005/01/20 17:12

L39	2	("6599366").URPN.	USPAT	OR	ON	2005/01/20 16:45
L40	4	("6413317" "6447608" "6530340" "6599366").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/01/20 16:45
L41	59	(semiconductor near2 wafer) and ((reduced near2 pressure) near10 unit) and "118"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L42	3	(semiconductor near2 wafer) and ((reduced near2 pressure) near10 unit) and cvd and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L43	55	"438"/\$.ccls. and module and (vacuum\$1 near2 chamber\$1) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L44	21	"118"/\$.ccls. and module and (vacuum\$1 near2 chamber\$1) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L45	3	"134"/\$.ccls. and module and (vacuum\$1 near2 chamber\$1) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L46	19	"118"/\$.ccls. and module and (low near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L47	8	"134"/\$.ccls. and module and (low near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L48	6	"204"/\$.ccls. and module and (low near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45

L49	114	"438"/\$.ccls. and module and (low near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L50	13	"118"/\$.ccls. and module and (reduced near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L51	63	"438"/\$.ccls. and module and (reduced near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L52	4	"134"/\$.ccls. and module and (reduced near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L53	3	"204"/\$.ccls. and module and (reduced near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L54	1	"396"/\$.ccls. and module and (low near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L55	8	"396"/\$.ccls. and module and (reduced near2 pressure) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L56	19	(semiconductor near2 wafer) and ((reduced near2 pressure) near10 unit) and (SOG or photoresist)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45

L57	74	"134"/\$.ccls. and module and (transfer near3 (mechanism or arm))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L58	0	"118"/\$.ccls. and (cluster near4 tool) and (transfer near3 (mechanism or arm)) and (atmosphere near10 control)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L59	0	"118"/\$.ccls. and (cluster near4 tool) and (transfer near3 (mechanism or arm)) and (atmosphere near10 control)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L60	1	(cluster near4 tool) and (transfer near3 (mechanism or arm)) and (atmosphere near10 control)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L61	22	(cluster near4 tool) and (atmosphere near10 control)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L62	431	(transfer near3 (mechanism or arm)) and (atmosphere near10 control)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L63	45	(transfer near3 (mechanism or arm)) and (atmosphere near10 control) and tokyo.asn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L64	435	(414/936).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45

L65	220	(118/713).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L66	324	(414/938).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L67	499	(414/941).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L68	740	(414/937).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L69	696	(414/939).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L70	919	(414/935).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L71	768	(414/940).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L72	29	(L70 L64 L68 L66 L69 L71 L67) and (cover near2 body)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45

L73	3	("5664254").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L74	23	(L70 L64 L68 L66 L69 L71 L67) and (cover near2 arm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L75	70	(transfer near3 (mechanism or arm)) same (cover near2 body)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L76	24	(wafer near3 (holder or arm)) same (cover near2 body)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L77	1329	(wafer near3 (holder or arm)) and (tokyo.asn.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L78	19	"414"/\$.ccls. and ((wafer near3 (holder or arm)) near5 cover)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L79	118	(wafer near3 (holder or arm)) and (tokyo.asn.) and (cover near4 wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L80	169	((wafer near3 (holder or arm)) near5 (cover))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45

L81	62	tokyo.asn. and (cover near2 arm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L82	35	iida.in. and nariaki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L83	535	tokyo.asn. and (cover near2 body)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L84	1104	(transfer near3 (mechanism or arm)) near12 (clean or cleaning)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L85	393	(414/414).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L86	178	(134/102.3).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L87	383	(134/95.2).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L88	801	(134/113).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45

L89	2	("5772386").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 16:45
L90	4853	(wafer near3 (holder or arm)) and (clean or cleaning)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L91	0	((transfer near3 (mechanism or arm)) near12 (ccd or camera)) and (stain near4 detect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L92	3	(transfer near3 (mechanism or arm)) near12 (stain near4 detect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L93	1	(wafer near3 (holder or arm)) near12 (stain near4 detect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L94	0	(wafer near3 (holder or arm)) near12 (deposit near4 detect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L95	0	(wafer near3 (holder or arm)) near12 (dirt near4 detect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L96	0	(wafer near3 (holder or arm)) near12 (waste near4 detect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45

L97	122	(transfer near3 (mechanism or arm)) near12 (clean or cleaning) and "134"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L98	8	"204"/\$.ccls. and module and (vacuum\$1 near2 chamber\$1) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L99	21	"118"/\$.ccls. and module and (vacuum\$1 near2 chamber\$1) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L100	3	"134"/\$.ccls. and module and (vacuum\$1 near2 chamber\$1) and (spin near2 (coat or coating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:45
L101	1	("5937223").PN.	USPAT	OR	OFF	2005/01/20 17:12